L Number	Hits	Search Text	DB	Time stamp
1	3321	((257/168) or (257/173) or (257/355) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 19:14
2	119	(((257/168) or (257/173) or (257/355) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (uniformly or evenly or uniform or even) near12 (distribution or distributed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 19:15
3	60	(((257/168) or (257/173) or (257/355) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (uniformly or evenly or uniform or even) near12 (distribution or distributed) and (esd or electrostatic adj discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 19:19
4	44	(((257/168) or (257/173) or (257/355) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (uniformly or evenly or uniform or even) near12 (distribution or distributed) and (esd or electrostatic adj discharge) and (resistor or resistance) near15 (transistor or fet or mis or mos or mosfet or misfet or igfet or jfet or dmos or dmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 19:22
-	92	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 17:40
-	312	(257/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:15
-	9	(("257/168").CCLS.) and (("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:15
-	4	plurality adj2 bipolar adj transistor.clm. and esd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:16
-	36	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:17
-	40	(plurality adj2 bipolar adj transistor.clm. and esd) or (((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:22
-	547	resistor and esd and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:23
-	117	resistor and esd and ((parallel or lateral$2) near3 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:34
-	152	charpentier.in.	EPO	2002/02/05 20:35

-		395	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 10:57
-		166	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:43
-		97	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:47
-		94	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:48
-		94	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect$3 or load))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:51
-		93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect$3 or load))and bipolar.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:51
-		93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect$3 or load))and bipolar.ti,ab. and (ic or integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:52
-		93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect$3 or load))and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:54
-		93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect$3) and (resist$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect$3 or load)) and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:54
-		31	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect$3.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:57
-		20	(((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect$3.ti,ab.) and bipolar adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:57

-	16	`(((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect$3.ti,ab.) and bipolar adj2 transistor) and resist$3`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 09:14
-	3	`5043782.pn.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 09:16
-	2	`5708550.pn.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 09:15
-	2	`jp-61292351$-$.did.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 09:16
-	395	`((257/168) or (257/173)).CCLS.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:37
-	0	`("L3 and esd adj2 protection.ti,ab.").PN.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 10:58
-	29	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 10:58
-	7	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 10:59
-	0	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 bipolar`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 10:59
-	0	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 transistor`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:00
-	15	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:00
-	12	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist$3`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:02
-	5	`((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist$3 and parallel`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:02
-	3	`((("257/168") or ("257/173")).CCLS.) and esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:48

-	131	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:49
-	1	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and plurality adj2 (bipolar or transistor) and resist$3 and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 14:06
-	12	esd adj protection.ti,ab. and ((advantage or purpose) near10 $3bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 14:08
-	1	("0708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:07
-	2	("5708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:35
-	7	(("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.	USPAT	2002/02/06 15:20
-	5	((("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.) and (base adj region and bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:21
-	0	("esd adj protection.ti,ab and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:35
-	0	("esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:36
-	48	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:38
-	17	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and current adj path	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 15:40
-	15	bipolar adj transistor and esd adj protection and (increase near12 path)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 16:49
-	12	bipolar adj transistor and esd adj protection and ((base near10 (surround$3 or enclos$3)) near10 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:01
-	710	bipolar adj transistor.ti,ab. and ((base near10 (surround$3 or enclos$3)) near10 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:04

-	506	bipolar adj transistor.ti,ab. and ((base near5 (surround$3 or enclos$3)) near5 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:05
-	334	bipolar adj transistor.ti,ab. and ((base near3 (surround$3 or enclos$3)) near3 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:05
-	2	bipolar adj transistor.ti,ab. and ((base near3 (surround$3 or enclos$3)) near3 (emitter or collector)) and esd.ti,ab. and protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:07
-	5	bipolar adj transistor.ti,ab. and ((base near4 (surround$3 or enclos$3)) near4 (emitter or collector)) and (electrostatic adj discharge or esd).ti,ab. and protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:10
-	430	bipolar adj transistor.ti,ab. and ((base near4 (surround$3 or enclos$3)) near4 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:11
-	6	bipolar adj transistor.ti,ab. and ((base near4 (surround$3 or enclos$3)) near4 (emitter or collector)) and (esd with protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:32
-	997	(257/355).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:33
-	95	(("257/355").CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:42
-	4	((("257/355").CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround$3 or enclos$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:39
-	1115	((257/360) or (257/361) or (257/362) or (257/363)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:38
-	122	((("257/360") or ("257/361") or ("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:39
-	6	(((("257/360") or ("257/361") or ("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround$3 or enclos$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:42
-	893	((257/370) or (257/373)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:41
-	7	((("257/370") or ("257/373")).CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 17:42

~	0	(((("257/370") or ("257/373")).CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround$3 or enclos$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 18:25
–	192	bipolar adj transistor.ti,ab. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 18:28
–	65	bipolar adj transistor.ti. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 18:42
–	2	lateral adj bipolar adj transistor.ti. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 18:45
–	15	lateral adj bipolar adj transistor.ti,ab. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 18:45
–	0	(source or drain) adj regions same through-contact$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/07 08:33
–	3	formed adj2 "same substrate" same plurality adj2 bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/07 10:01
–	4	(("5623387") or ("5043782") or ("6075271") or ("6277689")).PN.	USPAT	2002/02/07 10:02
–	0	jp-0361292351$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/07 10:04
–	0	jp-361292351$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/07 10:04
–	2	jp-61292351$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/07 10:04